

### General Description

The MDV3605 uses advanced MagnaChip's MOSFET Technology to provide low on-state resistance.

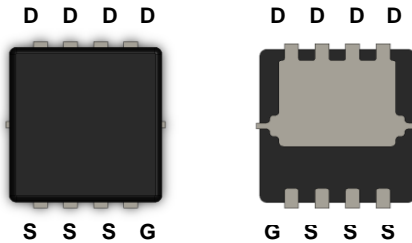
This device is suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

### Features

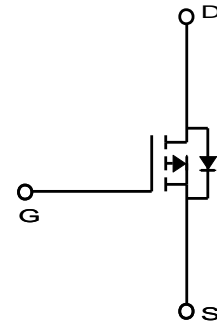
- $V_{DS} = -30V$
- $I_D = -20A$  @  $V_{GS} = -10V$
- $R_{DS(ON)} < 18.0m\Omega$  @  $V_{GS} = -10V$
- $R_{DS(ON)} < 33.0m\Omega$  @  $V_{GS} = -4.5V$

### Applications

- Load Switch
- General purpose applications
- Smart Module for Note PC Battery



PDFN33



### Absolute Maximum Ratings ( $T_a = 25^\circ C$ unless otherwise noted)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	-30	V
Gate-Source Voltage		$V_{GSS}$	$\pm 25$	V
Continuous Drain Current <sup>(1)</sup>	$T_C = 25^\circ C$ (Package limited)	$I_D$	-20.0	A
	$T_C = 25^\circ C$ (Silicon limited)		-29.0	
	$T_C = 70^\circ C$ (Silicon limited)		-24.0	
	$T_A = 25^\circ C$		-10.8 <sup>(3)</sup>	
	$T_A = 70^\circ C$		-8.8	
Pulsed Drain Current		$I_{DM}$	-80.0	A
Power Dissipation	$T_C = 25^\circ C$	$P_D$	25.0	W
	$T_C = 70^\circ C$		16	
	$T_A = 25^\circ C$		3.4 <sup>(3)</sup>	
	$T_A = 70^\circ C$		2.2	
Single Pulse Avalanche Energy <sup>(2)</sup>		$E_{AS}$	60.5	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	$^\circ C$

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	36	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.0	

## Ordering Information

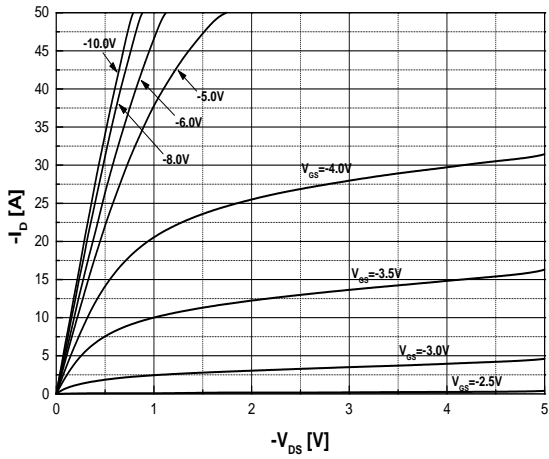
Part Number	Temp. Range	Package	Packing	RoHS Status
MDV3605URH	-55~150°C	PDFN33	Tape & Reel	Halogen Free

## Electrical Characteristics (T<sub>a</sub> = 25°C unless otherwise noted)

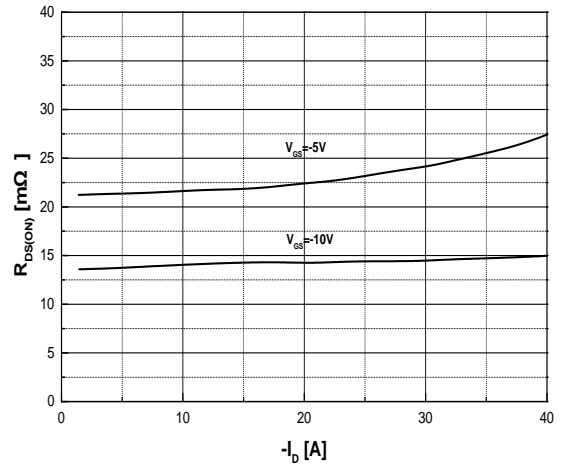
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-2.0	-3.0	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	-		-1	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V	-	-	±0.1	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -8A	-	14.0	18.0	mΩ
		V <sub>GS</sub> = -5.0V, I <sub>D</sub> = -8A		21.0	28.0	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -8A		25.0	33.0	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -10A		21.5	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -8A V <sub>GS</sub> = -10V	-	22.0	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.3	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	4.3	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	1035	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	150	-	
Output Capacitance	C <sub>oss</sub>		-	260	-	
Gate Resistance	R <sub>g</sub>	f = 1.0MHz	-	6.4	-	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -8A, R <sub>GEN</sub> = 3Ω	-	12.0	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	12.4	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	52.1	-	
Turn-Off Fall Time	t <sub>f</sub>		-	8.9	-	
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-0.71	-1.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -8A, di/dt = 100A/μs	-	30.8		ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	26.4	-	nC

Note :

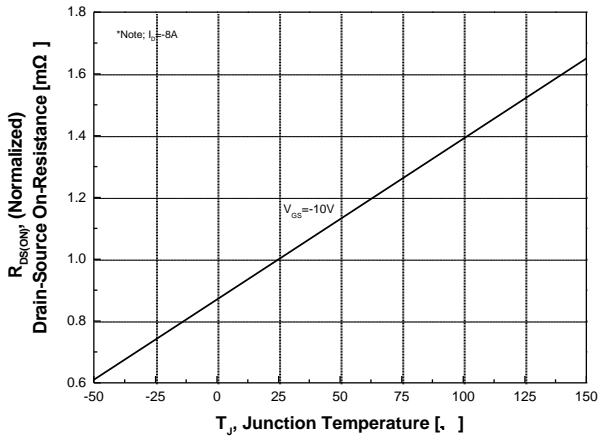
1. Surface mounted RF4 board with 2oz. Copper.
2. Starting T<sub>J</sub>=25°C, L=1.0mH, I<sub>AS</sub>= -11.0A V<sub>DD</sub>=-20.0V, V<sub>GS</sub>=-10.0V. Tested at I<sub>AS</sub>=-8.5A.
3. T < 10sec



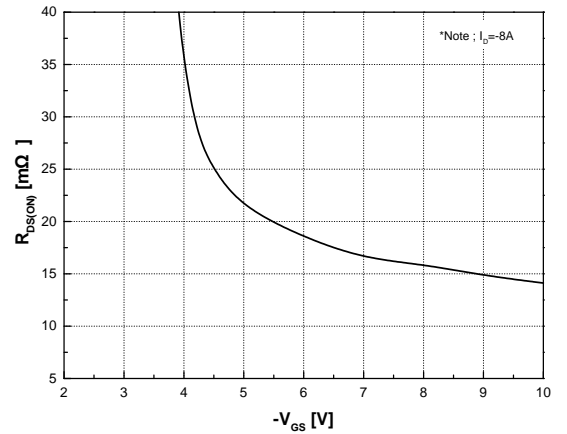
**Fig.1 On-Region Characteristics**



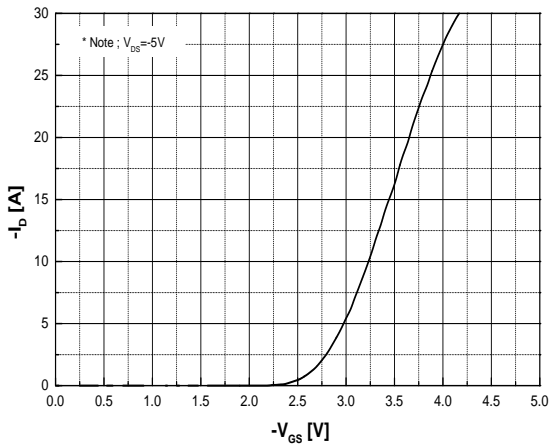
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



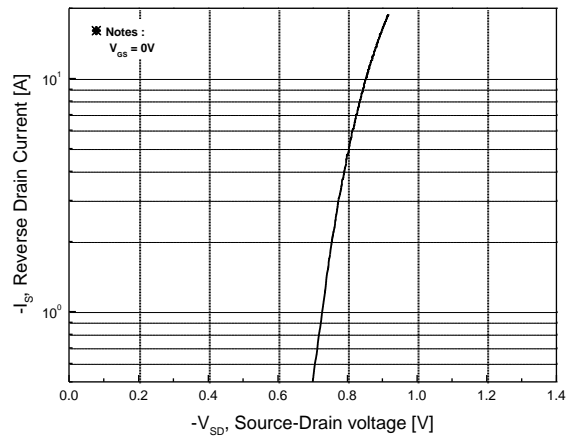
**Fig.3 On-Resistance Variation with Temperature**



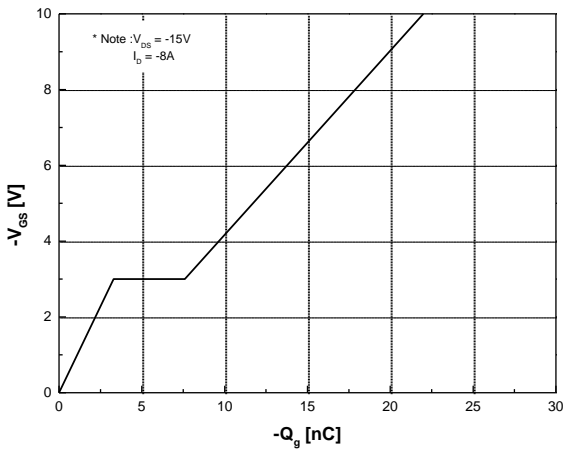
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



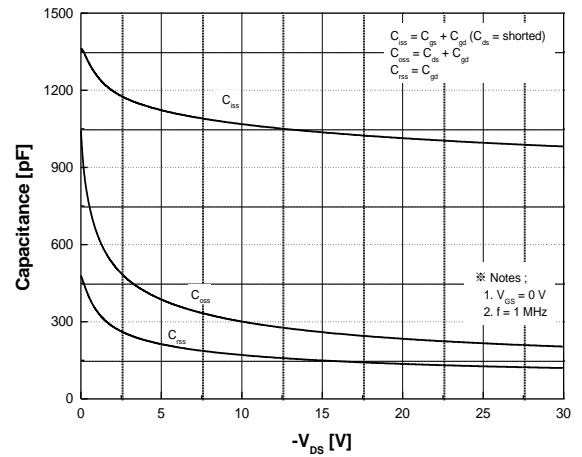
**Fig.5 Transfer Characteristics**



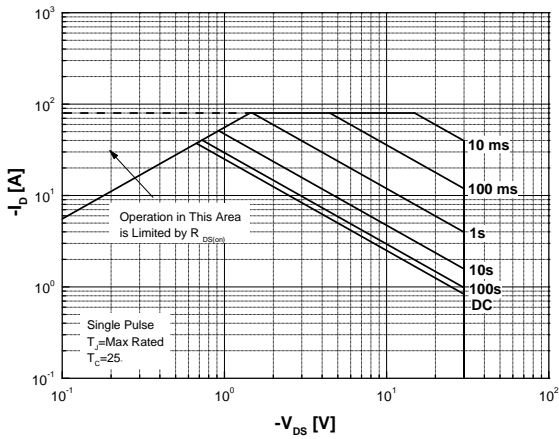
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



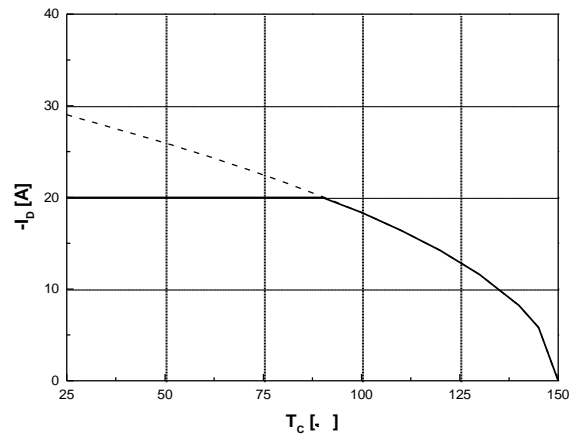
**Fig.7 Gate Charge Characteristics**



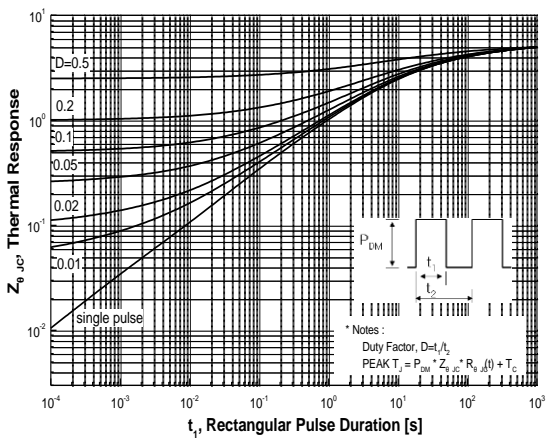
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Ambient Temperature**

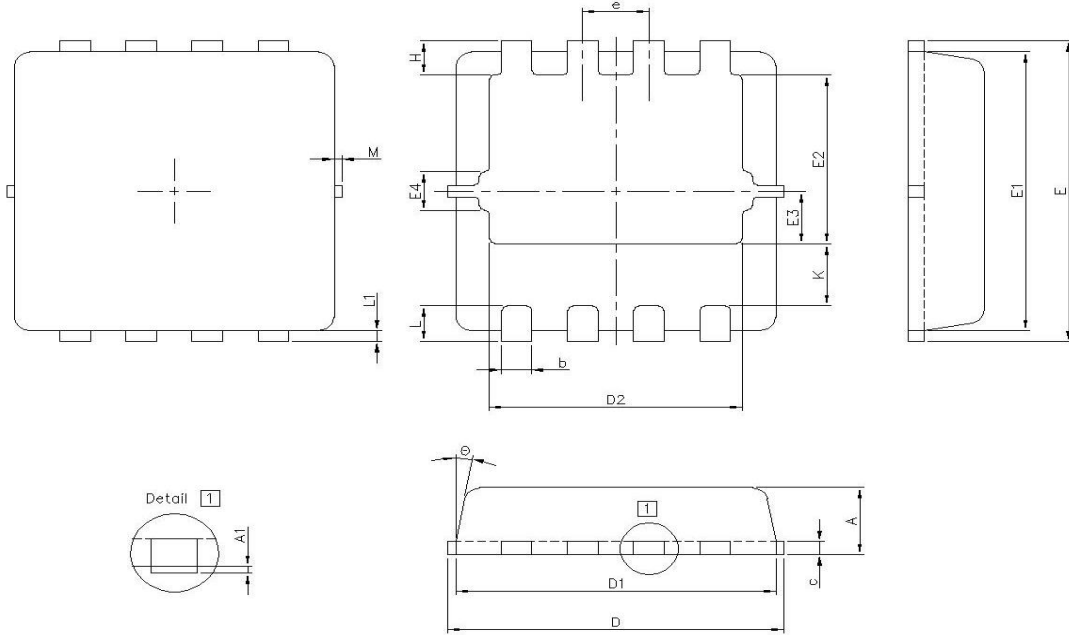


**Fig.11 Transient Thermal Response Curve**

**Package Dimension**

**PowerDFN33 (3.3x3.3mm)**

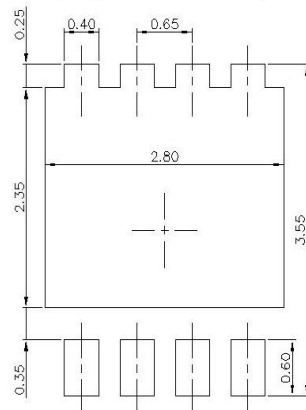
Dimensions are in millimeters, unless otherwise specified



(Unit: mm)


DIM	Min	Max	DIM	Min	Max
A	0.70	0.80	E2	1.78	1.98
A1	0.00	0.05	E3	0.49	0.69
b	0.25	0.35	E4	0.35 TYP.	
c	0.10	0.25	e	0.65 BSC	
D	3.20	3.40	K	0.70 TYP.	
D1	3.00	3.20	L	0.30	0.50
D2	2.39	2.59	L1	0.13 TYP.	
E	3.25	3.45	H	0.27	0.47
E1	3.00	3.20	⊕	0	12

Land Pattern  
(Only for Reference)



**DISCLAIMER:**

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

MagnaChip reserves the right to change the specifications and circuitry without notice at any time. MagnaChip does not consider responsibility for use of any circuitry other than circuitry entirely included in a MagnaChip product.  is a registered trademark of MagnaChip Semiconductor Ltd.